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Understanding **Embedded - FPGAs (Field Programmable Gate Array)**

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	18625
Number of Logic Elements/Cells	149000
Total RAM Bits	7014400
Number of I/O	586
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	1156-BBGA
Supplier Device Package	1156-FPBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-150ea-6lfn1156i

Architecture Overview

Each LatticeECP3 device contains an array of logic blocks surrounded by Programmable I/O Cells (PIC). Interspersed between the rows of logic blocks are rows of sysMEM™ Embedded Block RAM (EBR) and rows of sys-DSP™ Digital Signal Processing slices, as shown in Figure 2-1. The LatticeECP3-150 has four rows of DSP slices; all other LatticeECP3 devices have two rows of DSP slices. In addition, the LatticeECP3 family contains SERDES Quads on the bottom of the device.

There are two kinds of logic blocks, the Programmable Functional Unit (PFU) and Programmable Functional Unit without RAM (PFF). The PFU contains the building blocks for logic, arithmetic, RAM and ROM functions. The PFF block contains building blocks for logic, arithmetic and ROM functions. Both PFU and PFF blocks are optimized for flexibility, allowing complex designs to be implemented quickly and efficiently. Logic Blocks are arranged in a two-dimensional array. Only one type of block is used per row.

The LatticeECP3 devices contain one or more rows of sysMEM EBR blocks. sysMEM EBRs are large, dedicated 18Kbit fast memory blocks. Each sysMEM block can be configured in a variety of depths and widths as RAM or ROM. In addition, LatticeECP3 devices contain up to two rows of DSP slices. Each DSP slice has multipliers and adder/accumulators, which are the building blocks for complex signal processing capabilities.

The LatticeECP3 devices feature up to 16 embedded 3.2 Gbps SERDES (Serializer / Deserializer) channels. Each SERDES channel contains independent 8b/10b encoding / decoding, polarity adjust and elastic buffer logic. Each group of four SERDES channels, along with its Physical Coding Sub-layer (PCS) block, creates a quad. The functionality of the SERDES/PCS quads can be controlled by memory cells set during device configuration or by registers that are addressable during device operation. The registers in every quad can be programmed via the SERDES Client Interface (SCI). These quads (up to four) are located at the bottom of the devices.

Each PIC block encompasses two PIOs (PIO pairs) with their respective sysI/O buffers. The sysI/O buffers of the LatticeECP3 devices are arranged in seven banks, allowing the implementation of a wide variety of I/O standards. In addition, a separate I/O bank is provided for the programming interfaces. 50% of the PIO pairs on the left and right edges of the device can be configured as LVDS transmit/receive pairs. The PIC logic also includes pre-engineered support to aid in the implementation of high speed source synchronous standards such as XGMII, 7:1 LVDS, along with memory interfaces including DDR3.

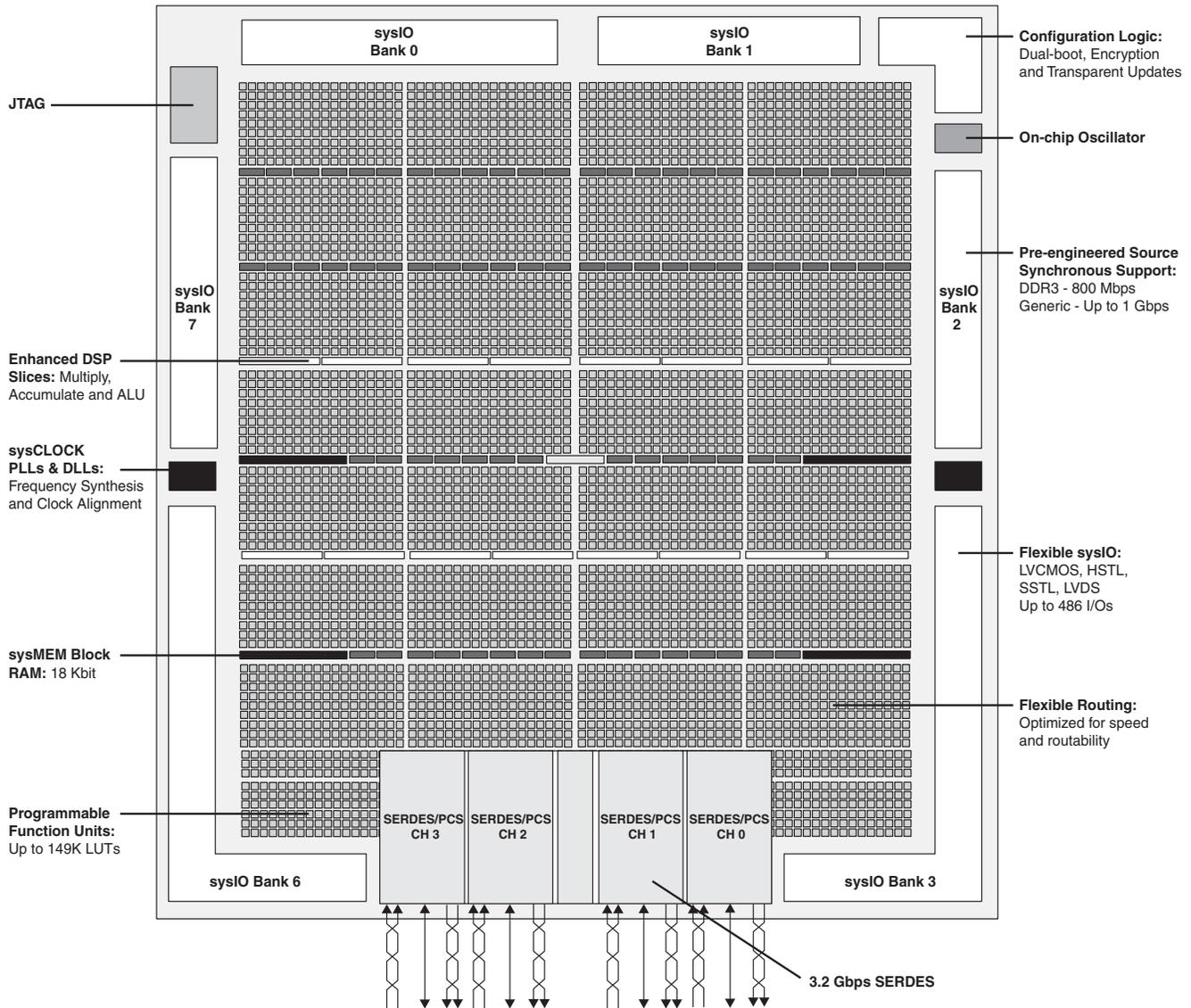
The LatticeECP3 registers in PFU and sysI/O can be configured to be SET or RESET. After power up and the device is configured, it enters into user mode with these registers SET/RESET according to the configuration setting, allowing the device entering to a known state for predictable system function.

Other blocks provided include PLLs, DLLs and configuration functions. The LatticeECP3 architecture provides two Delay Locked Loops (DLLs) and up to ten Phase Locked Loops (PLLs). The PLL and DLL blocks are located at the end of the EBR/DSP rows.

The configuration block that supports features such as configuration bit-stream decryption, transparent updates and dual-boot support is located toward the center of this EBR row. Every device in the LatticeECP3 family supports a sysCONFIG™ port located in the corner between banks one and two, which allows for serial or parallel device configuration.

In addition, every device in the family has a JTAG port. This family also provides an on-chip oscillator and soft error detect capability. The LatticeECP3 devices use 1.2 V as their core voltage.

Figure 2-1. Simplified Block Diagram, LatticeECP3-35 Device (Top Level)



Note: There is no Bank 4 or Bank 5 in LatticeECP3 devices.

PFU Blocks

The core of the LatticeECP3 device consists of PFU blocks, which are provided in two forms, the PFU and PFF. The PFUs can be programmed to perform Logic, Arithmetic, Distributed RAM and Distributed ROM functions. PFF blocks can be programmed to perform Logic, Arithmetic and ROM functions. Except where necessary, the remainder of this data sheet will use the term PFU to refer to both PFU and PFF blocks.

Each PFU block consists of four interconnected slices numbered 0-3 as shown in Figure 2-2. Each slice contains two LUTs. All the interconnections to and from PFU blocks are from routing. There are 50 inputs and 23 outputs associated with each PFU block.

The edge clocks on the top, left, and right sides of the device can drive the secondary clocks or general routing resources of the device. The left and right side edge clocks also can drive the primary clock network through the clock dividers (CLKDIV).

sysMEM Memory

LatticeECP3 devices contain a number of sysMEM Embedded Block RAM (EBR). The EBR consists of an 18-Kbit RAM with memory core, dedicated input registers and output registers with separate clock and clock enable. Each EBR includes functionality to support true dual-port, pseudo dual-port, single-port RAM, ROM and FIFO buffers (via external PFUs).

sysMEM Memory Block

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as shown in Table 2-7. FIFOs can be implemented in sysMEM EBR blocks by implementing support logic with PFUs. The EBR block facilitates parity checking by supporting an optional parity bit for each data byte. EBR blocks provide byte-enable support for configurations with 18-bit and 36-bit data widths. For more information, please see TN1179, [LatticeECP3 Memory Usage Guide](#).

Table 2-7. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36
True Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18
Pseudo Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

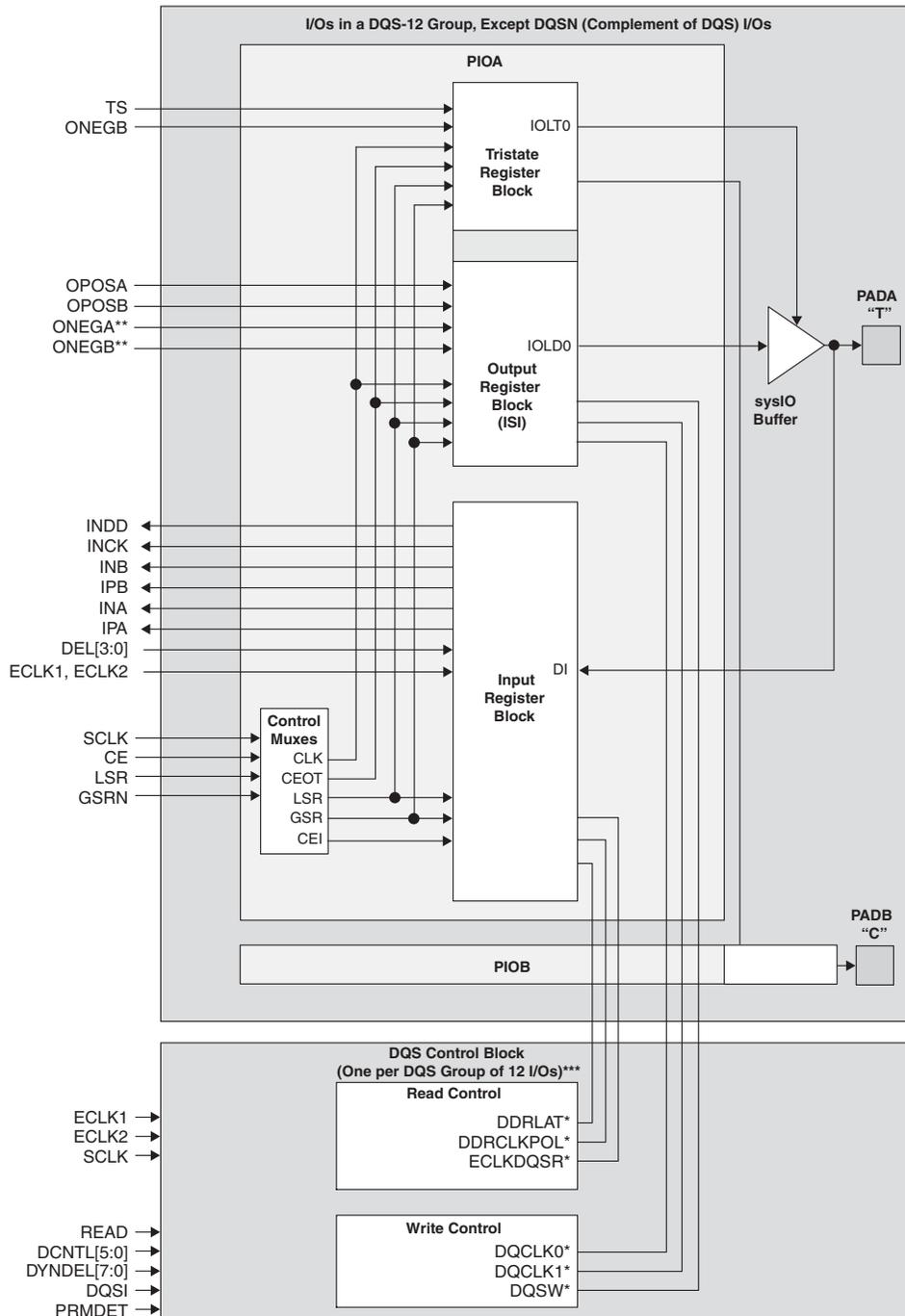
Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

Programmable I/O Cells (PIC)

Each PIC contains two PIOs connected to their respective sysI/O buffers as shown in Figure 2-32. The PIO Block supplies the output data (DO) and the tri-state control signal (TO) to the sysI/O buffer and receives input from the buffer. Table 2-11 provides the PIO signal list.

Figure 2-32. PIC Diagram



* Signals are available on left/right/top edges only.
 ** Signals are available on the left and right sides only
 *** Selected PIO.

Two adjacent PIOs can be joined to provide a differential I/O pair (labeled as “T” and “C”) as shown in Figure 2-32. The PAD Labels “T” and “C” distinguish the two PIOs. Approximately 50% of the PIO pairs on the left and right edges of the device can be configured as true LVDS outputs. All I/O pairs can operate as LVDS inputs.

Table 2-11. PIO Signal List

Name	Type	Description
INDD	Input Data	Register bypassed input. This is not the same port as INCK.
IPA, INA, IPB, INB	Input Data	Ports to core for input data
OPOSA, ONEGA ¹ , OPOSB, ONEGB ¹	Output Data	Output signals from core. An exception is the ONEGB port, used for tristate logic at the DQS pad.
CE	PIO Control	Clock enables for input and output block flip-flops.
SCLK	PIO Control	System Clock (PCLK) for input and output/TS blocks. Connected from clock ISB.
LSR	PIO Control	Local Set/Reset
ECLK1, ECLK2	PIO Control	Edge clock sources. Entire PIO selects one of two sources using mux.
ECLKDQSR ¹	Read Control	From DQS_STROBE, shifted strobe for memory interfaces only.
DDRCLKPOL ¹	Read Control	Ensures transfer from DQS domain to SCLK domain.
DDRLAT ¹	Read Control	Used to guarantee INDDR2 gearing by selectively enabling a D-Flip-Flop in datapath.
DEL[3:0]	Read Control	Dynamic input delay control bits.
INCK	To Clock Distribution and PLL	PIO treated as clock PIO, path to distribute to primary clocks and PLL.
TS	Tristate Data	Tristate signal from core (SDR)
DQCLK0 ¹ , DQCLK1 ¹	Write Control	Two clocks edges, 90 degrees out of phase, used in output gearing.
DQSW ²	Write Control	Used for output and tristate logic at DQS only.
DYNDEL[7:0]	Write Control	Shifting of write clocks for specific DQS group, using 6:0 each step is approximately 25ps, 128 steps. Bit 7 is an invert (timing depends on input frequency). There is also a static control for this 8-bit setting, enabled with a memory cell.
DCNTL[6:0]	PIO Control	Original delay code from DDR DLL
DATAVALID ¹	Output Data	Status flag from DATAVALID logic, used to indicate when input data is captured in IOLOGIC and valid to core.
READ	For DQS_Strobe	Read signal for DDR memory interface
DQSI	For DQS_Strobe	Unshifted DQS strobe from input pad
PRMBDET	For DQS_Strobe	DQSI biased to go high when DQSI is tristate, goes to input logic block as well as core logic.
GSRN	Control from routing	Global Set/Reset

1. Signals available on left/right/top edges only.

2. Selected PIO.

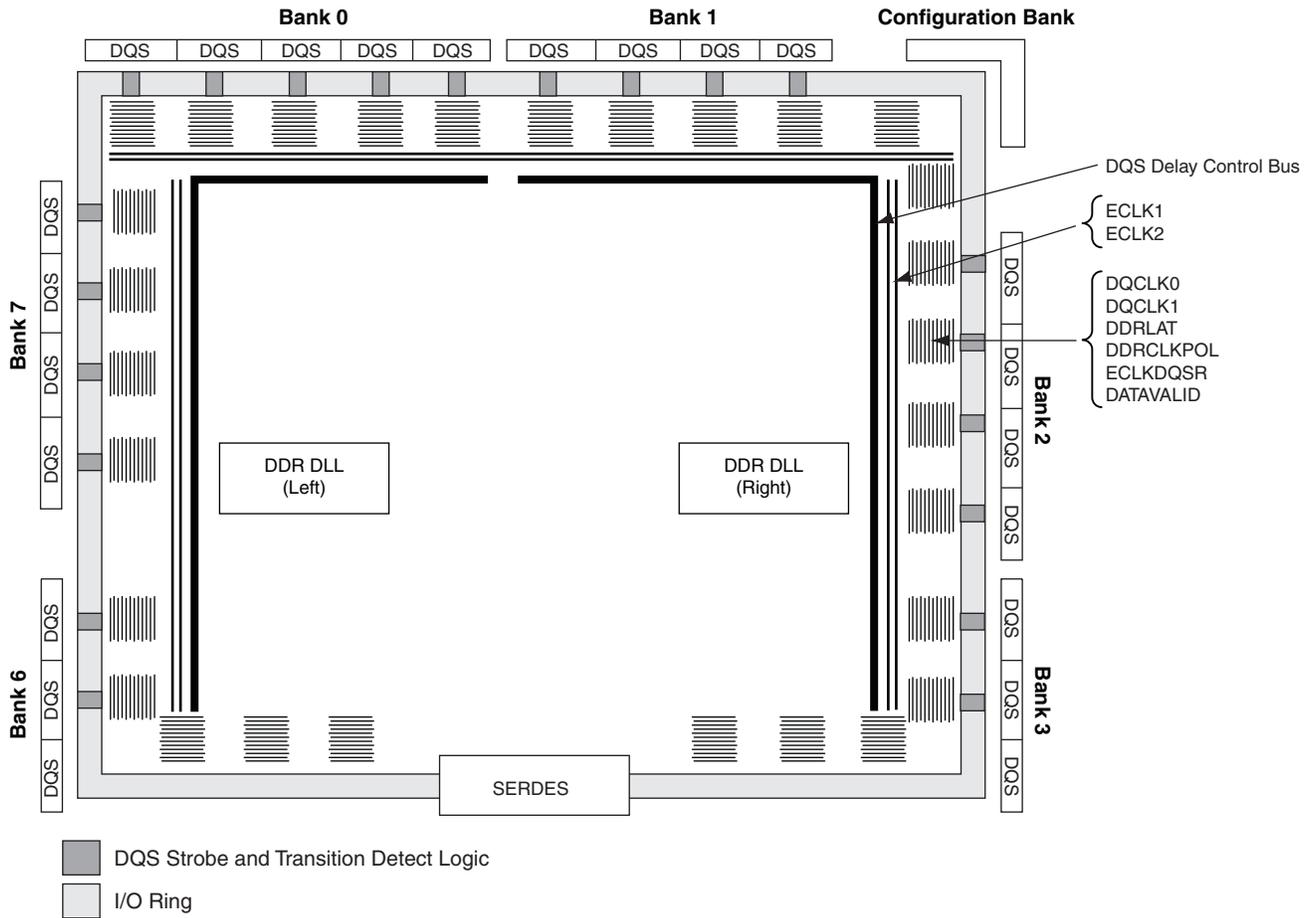
PIO

The PIO contains four blocks: an input register block, output register block, tristate register block and a control logic block. These blocks contain registers for operating in a variety of modes along with the necessary clock and selection logic.

Input Register Block

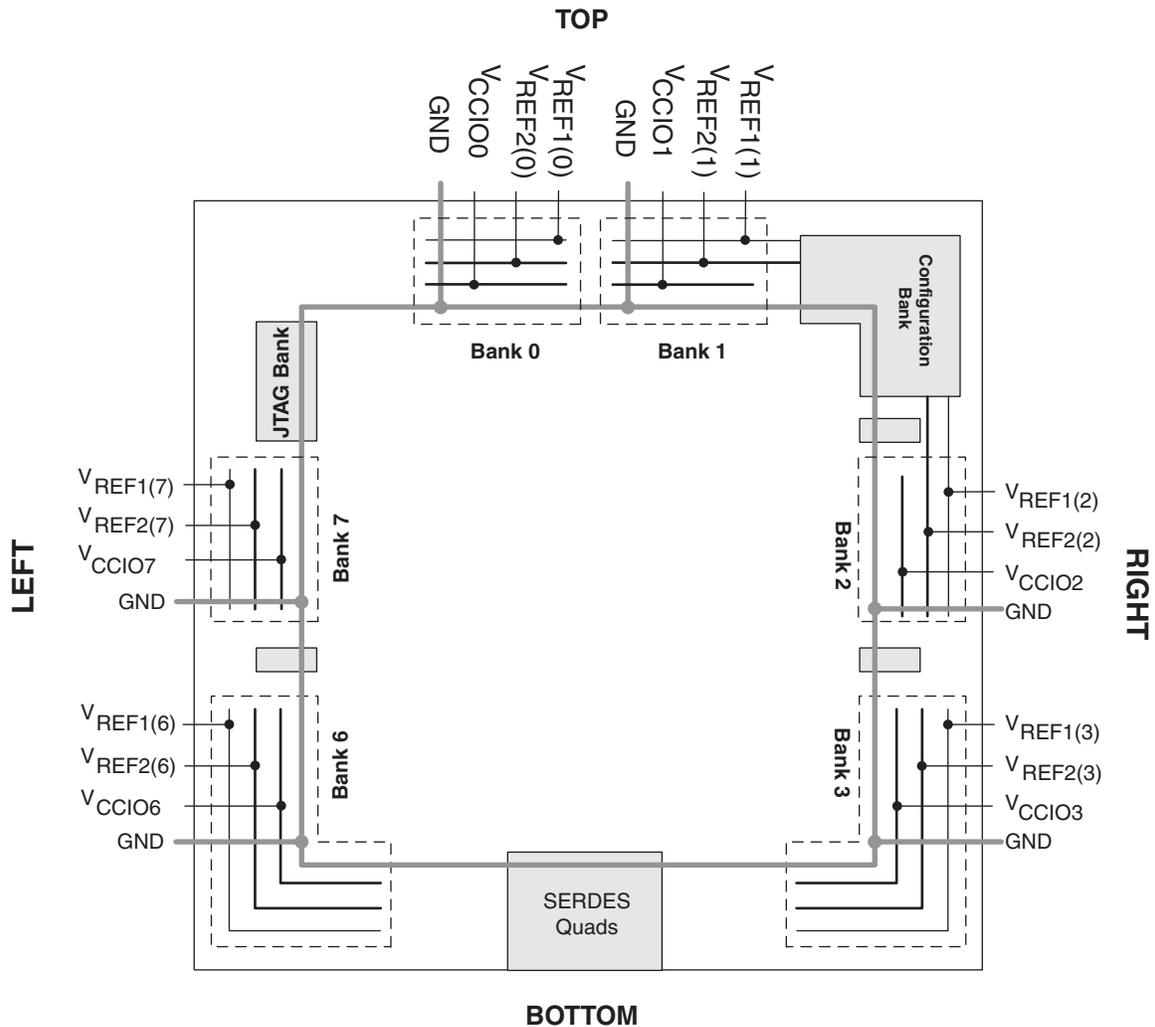
The input register blocks for the PIOs, in the left, right and top edges, contain delay elements and registers that can be used to condition high-speed interface signals, such as DDR memory interfaces and source synchronous interfaces, before they are passed to the device core. Figure 2-33 shows the input register block for the left, right and top edges. The input register block for the bottom edge contains one element to register the input signal and no DDR registers. The following description applies to the input register block for PIOs in the left, right and top edges only.

Figure 2-36. Edge Clock, DLL Calibration and DQS Local Bus Distribution



*Includes shared configuration I/Os and dedicated configuration I/Os.

Figure 2-38. LatticeECP3 Banks



LatticeECP3 devices contain two types of sysI/O buffer pairs.

1. Top (Bank 0 and Bank 1) and Bottom sysI/O Buffer Pairs (Single-Ended Outputs Only)

The sysI/O buffer pairs in the top banks of the device consist of two single-ended output drivers and two sets of single-ended input buffers (both ratioed and referenced). One of the referenced input buffers can also be configured as a differential input. Only the top edge buffers have a programmable PCI clamp.

The two pads in the pair are described as “true” and “comp”, where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

The top and bottom sides are ideal for general purpose I/O, PCI, and inputs for LVDS (LVDS outputs are only allowed on the left and right sides). The top side can be used for the DDR3 ADDR/CMD signals.

The I/O pins located on the top and bottom sides of the device (labeled PTxxA/B or PBxxA/B) are fully hot socketable. Note that the pads in Banks 3, 6 and 8 are wrapped around the corner of the device. In these banks, only the pads located on the top or bottom of the device are hot socketable. The top and bottom side pads can be identified by the Lattice Diamond tool.

SCI (SERDES Client Interface) Bus

The SERDES Client Interface (SCI) is an IP interface that allows the SERDES/PCS Quad block to be controlled by registers rather than the configuration memory cells. It is a simple register configuration interface that allows SERDES/PCS configuration without power cycling the device.

The Diamond and ispLEVER design tools support all modes of the PCS. Most modes are dedicated to applications associated with a specific industry standard data protocol. Other more general purpose modes allow users to define their own operation. With these tools, the user can define the mode for each quad in a design.

Popular standards such as 10Gb Ethernet, x4 PCI Express and 4x Serial RapidIO can be implemented using IP (available through Lattice), a single quad (Four SERDES channels and PCS) and some additional logic from the core.

The LatticeECP3 family also supports a wide range of primary and secondary protocols. Within the same quad, the LatticeECP3 family can support mixed protocols with semi-independent clocking as long as the required clock frequencies are integer x1, x2, or x11 multiples of each other. Table 2-15 lists the allowable combination of primary and secondary protocol combinations.

Flexible Quad SERDES Architecture

The LatticeECP3 family SERDES architecture is a quad-based architecture. For most SERDES settings and standards, the whole quad (consisting of four SERDES) is treated as a unit. This helps in silicon area savings, better utilization and overall lower cost.

However, for some specific standards, the LatticeECP3 quad architecture provides flexibility; more than one standard can be supported within the same quad.

Table 2-15 shows the standards can be mixed and matched within the same quad. In general, the SERDES standards whose nominal data rates are either the same or a defined subset of each other, can be supported within the same quad. In Table 2-15, the Primary Protocol column refers to the standard that determines the reference clock and PLL settings. The Secondary Protocol column shows the other standard that can be supported within the same quad.

Furthermore, Table 2-15 also implies that more than two standards in the same quad can be supported, as long as they conform to the data rate and reference clock requirements. For example, a quad may contain PCI Express 1.1, SGMII, Serial RapidIO Type I and Serial RapidIO Type II, all in the same quad.

Table 2-15. LatticeECP3 Primary and Secondary Protocol Support

Primary Protocol	Secondary Protocol
PCI Express 1.1	SGMII
PCI Express 1.1	Gigabit Ethernet
PCI Express 1.1	Serial RapidIO Type I
PCI Express 1.1	Serial RapidIO Type II
Serial RapidIO Type I	SGMII
Serial RapidIO Type I	Gigabit Ethernet
Serial RapidIO Type II	SGMII
Serial RapidIO Type II	Gigabit Ethernet
Serial RapidIO Type II	Serial RapidIO Type I
CPRI-3	CPRI-2 and CPRI-1
3G-SDI	HD-SDI and SD-SDI

LatticeECP3 Supply Current (Standby)^{1, 2, 3, 4, 5, 6}
Over Recommended Operating Conditions

Symbol	Parameter	Device	Typical		Units
			-6L, -7L, -8L	-6, -7, -8	
I _{CC}	Core Power Supply Current	ECP-17EA	29.8	49.4	mA
		ECP3-35EA	53.7	89.4	mA
		ECP3-70EA	137.3	230.7	mA
		ECP3-95EA	137.3	230.7	mA
		ECP3-150EA	219.5	370.9	mA
I _{CCAUX}	Auxiliary Power Supply Current	ECP-17EA	18.3	19.4	mA
		ECP3-35EA	19.6	23.1	mA
		ECP3-70EA	26.5	32.4	mA
		ECP3-95EA	26.5	32.4	mA
		ECP3-150EA	37.0	45.7	mA
I _{CCPLL}	PLL Power Supply Current (Per PLL)	ECP-17EA	0.0	0.0	mA
		ECP3-35EA	0.1	0.1	mA
		ECP3-70EA	0.1	0.1	mA
		ECP3-95EA	0.1	0.1	mA
		ECP3-150EA	0.1	0.1	mA
I _{CCIO}	Bank Power Supply Current (Per Bank)	ECP-17EA	1.3	1.4	mA
		ECP3-35EA	1.3	1.4	mA
		ECP3-70EA	1.4	1.5	mA
		ECP3-95EA	1.4	1.5	mA
		ECP3-150EA	1.4	1.5	mA
I _{CCJ}	JTAG Power Supply Current	All Devices	2.5	2.5	mA
I _{CCA}	Transmit, Receive, PLL and Reference Clock Buffer Power Supply	ECP-17EA	6.1	6.1	mA
		ECP3-35EA	6.1	6.1	mA
		ECP3-70EA	18.3	18.3	mA
		ECP3-95EA	18.3	18.3	mA
		ECP3-150EA	24.4	24.4	mA

1. For further information on supply current, please see the list of technical documentation at the end of this data sheet.
2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at the V_{CCIO} or GND.
3. Frequency 0 MHz.
4. Pattern represents a "blank" configuration data file.
5. T_J = 85 °C, power supplies at nominal voltage.
6. To determine the LatticeECP3 peak start-up current data, use the Power Calculator tool.

sysI/O Recommended Operating Conditions

Standard	V _{CCIO}			V _{REF} (V)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
LVCMOS33 ²	3.135	3.3	3.465	—	—	—
LVCMOS33D	3.135	3.3	3.465	—	—	—
LVCMOS25 ²	2.375	2.5	2.625	—	—	—
LVCMOS18	1.71	1.8	1.89	—	—	—
LVCMOS15	1.425	1.5	1.575	—	—	—
LVCMOS12 ²	1.14	1.2	1.26	—	—	—
LVTTTL33 ²	3.135	3.3	3.465	—	—	—
PCI33	3.135	3.3	3.465	—	—	—
SSTL15 ³	1.43	1.5	1.57	0.68	0.75	0.9
SSTL18_I, II ²	1.71	1.8	1.89	0.833	0.9	0.969
SSTL25_I, II ²	2.375	2.5	2.625	1.15	1.25	1.35
SSTL33_I, II ²	3.135	3.3	3.465	1.3	1.5	1.7
HSTL15_I ²	1.425	1.5	1.575	0.68	0.75	0.9
HSTL18_I, II ²	1.71	1.8	1.89	0.816	0.9	1.08
LVDS25 ²	2.375	2.5	2.625	—	—	—
LVDS25E	2.375	2.5	2.625	—	—	—
MLVDS ¹	2.375	2.5	2.625	—	—	—
LVPECL33 ^{1, 2}	3.135	3.3	3.465	—	—	—
Mini LVDS	2.375	2.5	2.625	—	—	—
BLVDS25 ^{1, 2}	2.375	2.5	2.625	—	—	—
RSDS ²	2.375	2.5	2.625	—	—	—
RSDSE ^{1, 2}	2.375	2.5	2.625	—	—	—
TRLVDS	3.14	3.3	3.47	—	—	—
PPLVDS	3.14/2.25	3.3/2.5	3.47/2.75	—	—	—
SSTL15D ³	1.43	1.5	1.57	—	—	—
SSTL18D_I ^{2, 3} , II ^{2, 3}	1.71	1.8	1.89	—	—	—
SSTL25D_I ² , II ²	2.375	2.5	2.625	—	—	—
SSTL33D_I ² , II ²	3.135	3.3	3.465	—	—	—
HSTL15D_I ²	1.425	1.5	1.575	—	—	—
HSTL18D_I ² , II ²	1.71	1.8	1.89	—	—	—

1. Inputs on chip. Outputs are implemented with the addition of external resistors.
2. For input voltage compatibility, see TN1177, [LatticeECP3 sysIO Usage Guide](#).
3. VREF is required when using Differential SSTL to interface to DDR memory.

LVPECL33

The LatticeECP3 devices support the differential LVPECL standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The LVPECL input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-3 is one possible solution for point-to-point signals.

Figure 3-3. Differential LVPECL33

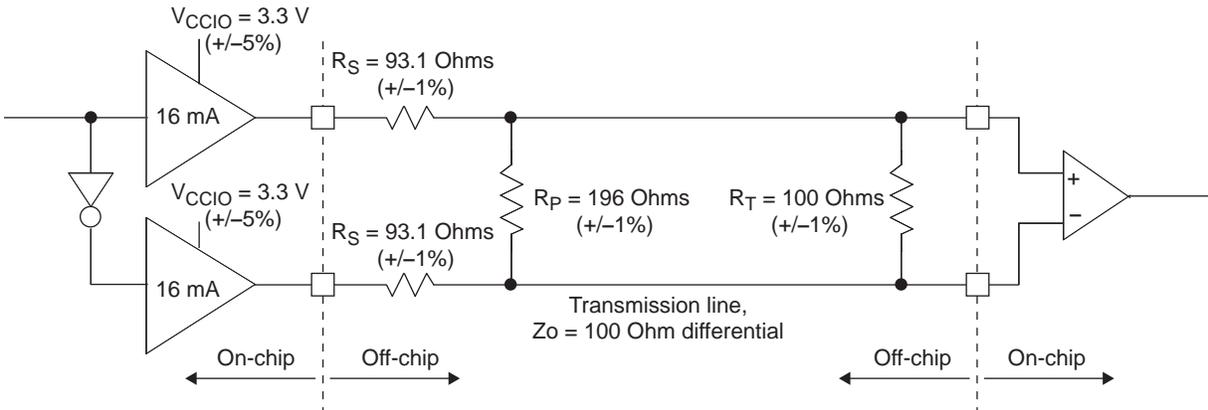


Table 3-3. LVPECL33 DC Conditions¹

Over Recommended Operating Conditions

Parameter	Description	Typical	Units
V_{CCIO}	Output Driver Supply ($\pm 5\%$)	3.30	V
Z_{OUT}	Driver Impedance	10	Ω
R_S	Driver Series Resistor ($\pm 1\%$)	93	Ω
R_P	Driver Parallel Resistor ($\pm 1\%$)	196	Ω
R_T	Receiver Termination ($\pm 1\%$)	100	Ω
V_{OH}	Output High Voltage	2.05	V
V_{OL}	Output Low Voltage	1.25	V
V_{OD}	Output Differential Voltage	0.80	V
V_{CM}	Output Common Mode Voltage	1.65	V
Z_{BACK}	Back Impedance	100.5	Ω
I_{DC}	DC Output Current	12.11	mA

1. For input buffer, see LVDS table.

Typical Building Block Function Performance

Pin-to-Pin Performance (LVCMOS25 12 mA Drive)^{1, 2, 3}

Function	-8 Timing	Units
Basic Functions		
16-bit Decoder	4.7	ns
32-bit Decoder	4.7	ns
64-bit Decoder	5.7	ns
4:1 MUX	4.1	ns
8:1 MUX	4.3	ns
16:1 MUX	4.7	ns
32:1 MUX	4.8	ns

1. These functions were generated using the ispLEVER design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.
2. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond or ispLEVER software.

Register-to-Register Performance^{1, 2, 3}

Function	-8 Timing	Units
Basic Functions		
16-bit Decoder	500	MHz
32-bit Decoder	500	MHz
64-bit Decoder	500	MHz
4:1 MUX	500	MHz
8:1 MUX	500	MHz
16:1 MUX	500	MHz
32:1 MUX	445	MHz
8-bit adder	500	MHz
16-bit adder	500	MHz
64-bit adder	305	MHz
16-bit counter	500	MHz
32-bit counter	460	MHz
64-bit counter	320	MHz
64-bit accumulator	315	MHz
Embedded Memory Functions		
512x36 Single Port RAM, EBR Output Registers	340	MHz
1024x18 True-Dual Port RAM (Write Through or Normal, EBR Output Registers)	340	MHz
1024x18 True-Dual Port RAM (Read-Before-Write, EBR Output Registers)	130	MHz
1024x18 True-Dual Port RAM (Write Through or Normal, PLC Output Registers)	245	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (One PFU)	500	MHz
32x4 Pseudo-Dual Port RAM	500	MHz
64x8 Pseudo-Dual Port RAM	400	MHz
DSP Function		
18x18 Multiplier (All Registers)	400	MHz
9x9 Multiplier (All Registers)	400	MHz
36x36 Multiply (All Registers)	260	MHz

LatticeECP3 External Switching Characteristics ^{1, 2, 3, 13}

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	-8		-7		-6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Clocks									
Primary Clock⁶									
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-150EA	—	500	—	420	—	375	MHz
t _{W_PRI}	Clock Pulse Width for Primary Clock	ECP3-150EA	0.8	—	0.9	—	1.0	—	ns
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-150EA	—	300	—	330	—	360	ps
t _{SKEW_PRIIB}	Primary Clock Skew Within a Bank	ECP3-150EA	—	250	—	280	—	300	ps
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-70EA/95EA	—	500	—	420	—	375	MHz
t _{W_PRI}	Pulse Width for Primary Clock	ECP3-70EA/95EA	0.8	—	0.9	—	1.0	—	ns
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-70EA/95EA	—	360	—	370	—	380	ps
t _{SKEW_PRIIB}	Primary Clock Skew Within a Bank	ECP3-70EA/95EA	—	310	—	320	—	330	ps
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-35EA	—	500	—	420	—	375	MHz
t _{W_PRI}	Pulse Width for Primary Clock	ECP3-35EA	0.8	—	0.9	—	1.0	—	ns
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-35EA	—	300	—	330	—	360	ps
t _{SKEW_PRIIB}	Primary Clock Skew Within a Bank	ECP3-35EA	—	250	—	280	—	300	ps
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-17EA	—	500	—	420	—	375	MHz
t _{W_PRI}	Pulse Width for Primary Clock	ECP3-17EA	0.8	—	0.9	—	1.0	—	ns
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-17EA	—	310	—	340	—	370	ps
t _{SKEW_PRIIB}	Primary Clock Skew Within a Bank	ECP3-17EA	—	220	—	230	—	240	ps
Edge Clock⁶									
f _{MAX_EDGE}	Frequency for Edge Clock	ECP3-150EA	—	500	—	420	—	375	MHz
t _{W_EDGE}	Clock Pulse Width for Edge Clock	ECP3-150EA	0.9	—	1.0	—	1.2	—	ns
t _{SKEW_EDGE_DQS}	Edge Clock Skew Within an Edge of the Device	ECP3-150EA	—	200	—	210	—	220	ps
f _{MAX_EDGE}	Frequency for Edge Clock	ECP3-70EA/95EA	—	500	—	420	—	375	MHz
t _{W_EDGE}	Clock Pulse Width for Edge Clock	ECP3-70EA/95EA	0.9	—	1.0	—	1.2	—	ns
t _{SKEW_EDGE_DQS}	Edge Clock Skew Within an Edge of the Device	ECP3-70EA/95EA	—	200	—	210	—	220	ps
f _{MAX_EDGE}	Frequency for Edge Clock	ECP3-35EA	—	500	—	420	—	375	MHz
t _{W_EDGE}	Clock Pulse Width for Edge Clock	ECP3-35EA	0.9	—	1.0	—	1.2	—	ns
t _{SKEW_EDGE_DQS}	Edge Clock Skew Within an Edge of the Device	ECP3-35EA	—	200	—	210	—	220	ps
f _{MAX_EDGE}	Frequency for Edge Clock	ECP3-17EA	—	500	—	420	—	375	MHz
t _{W_EDGE}	Clock Pulse Width for Edge Clock	ECP3-17EA	0.9	—	1.0	—	1.2	—	ns
t _{SKEW_EDGE_DQS}	Edge Clock Skew Within an Edge of the Device	ECP3-17EA	—	200	—	210	—	220	ps
Generic SDR									
General I/O Pin Parameters Using Dedicated Clock Input Primary Clock Without PLL²									
t _{CO}	Clock to Output - PIO Output Register	ECP3-150EA	—	3.9	—	4.3	—	4.7	ns
t _{SU}	Clock to Data Setup - PIO Input Register	ECP3-150EA	0.0	—	0.0	—	0.0	—	ns
t _H	Clock to Data Hold - PIO Input Register	ECP3-150EA	1.5	—	1.7	—	2.0	—	ns
t _{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-150EA	1.3	—	1.5	—	1.7	—	ns

LatticeECP3 External Switching Characteristics (Continued)^{1, 2, 3, 13}

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	-8		-7		-6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic DDRX2 Inputs with Clock and Data (>10bits wide) are Aligned at Pin (GDDR2_RX.ECLK.Aligned) (No CLKDIV)									
Left and Right Sides Using DLLCLKPIN for Clock Input									
t _{DVACLGDDR}	Data Setup Before CLK	ECP3-150EA	—	0.225	—	0.225	—	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-150EA	0.775	—	0.775	—	0.775	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA	—	460	—	385	—	345	MHz
t _{DVACLGDDR}	Data Setup Before CLK	ECP3-70EA/95EA	—	0.225	—	0.225	—	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-70EA/95EA	0.775	—	0.775	—	0.775	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-70EA/95EA	—	460	—	385	—	311	MHz
t _{DVACLGDDR}	Data Setup Before CLK	ECP3-35EA	—	0.210	—	0.210	—	0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-35EA	0.790	—	0.790	—	0.790	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-35EA	—	460	—	385	—	311	MHz
t _{DVACLGDDR}	Data Setup Before CLK (Left and Right Sides)	ECP3-17EA	—	0.210	—	0.210	—	0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-17EA	0.790	—	0.790	—	0.790	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-17EA	—	460	—	385	—	311	MHz
Top Side Using PCLK Pin for Clock Input									
t _{DVACLGDDR}	Data Setup Before CLK	ECP3-150EA	—	0.225	—	0.225	—	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-150EA	0.775	—	0.775	—	0.775	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA	—	235	—	170	—	130	MHz
t _{DVACLGDDR}	Data Setup Before CLK	ECP3-70EA/95EA	—	0.225	—	0.225	—	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-70EA/95EA	0.775	—	0.775	—	0.775	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-70EA/95EA	—	235	—	170	—	130	MHz
t _{DVACLGDDR}	Data Setup Before CLK	ECP3-35EA	—	0.210	—	0.210	—	0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-35EA	0.790	—	0.790	—	0.790	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-35EA	—	235	—	170	—	130	MHz
t _{DVACLGDDR}	Data Setup Before CLK	ECP3-17EA	—	0.210	—	0.210	—	0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-17EA	0.790	—	0.790	—	0.790	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-17EA	—	235	—	170	—	130	MHz
Generic DDRX2 Inputs with Clock and Data (<10 Bits Wide) Centered at Pin (GDDR2_RX.DQS.Centered) Using DQS Pin for Clock Input									
Left and Right Sides									
t _{SUGDDR}	Data Setup Before CLK	All ECP3EA Devices	330	—	330	—	352	—	ps
t _{HOGDDR}	Data Hold After CLK	All ECP3EA Devices	330	—	330	—	352	—	ps
f _{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	—	400	—	400	—	375	MHz
Generic DDRX2 Inputs with Clock and Data (<10 Bits Wide) Aligned at Pin (GDDR2_RX.DQS.Aligned) Using DQS Pin for Clock Input									
Left and Right Sides									
t _{DVACLGDDR}	Data Setup Before CLK	All ECP3EA Devices	—	0.225	—	0.225	—	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	All ECP3EA Devices	0.775	—	0.775	—	0.775	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	—	400	—	400	—	375	MHz
Generic DDRX1 Output with Clock and Data (>10 Bits Wide) Centered at Pin (GDDR1_TX.SCLK.Centered)¹⁰									
t _{DVBGDDR}	Data Valid Before CLK	ECP3-150EA	670	—	670	—	670	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-150EA	670	—	670	—	670	—	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA	—	250	—	250	—	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-70EA/95EA	666	—	665	—	664	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-70EA/95EA	666	—	665	—	664	—	ps

LatticeECP3 Internal Switching Characteristics^{1, 2, 5}

Over Recommended Commercial Operating Conditions

Parameter	Description	-8		-7		-6		Units.
		Min.	Max.	Min.	Max.	Min.	Max.	
PFU/PFF Logic Mode Timing								
t _{LUT4_PFU}	LUT4 delay (A to D inputs to F output)	—	0.147	—	0.163	—	0.179	ns
t _{LUT6_PFU}	LUT6 delay (A to D inputs to OFX output)	—	0.281	—	0.335	—	0.379	ns
t _{LSR_PFU}	Set/Reset to output of PFU (Asynchronous)	—	0.593	—	0.674	—	0.756	ns
t _{LSRREC_PFU}	Asynchronous Set/Reset recovery time for PFU Logic		0.298		0.345		0.391	ns
t _{SUM_PFU}	Clock to Mux (M0,M1) Input Setup Time	0.134	—	0.144	—	0.153	—	ns
t _{HM_PFU}	Clock to Mux (M0,M1) Input Hold Time	-0.097	—	-0.103	—	-0.109	—	ns
t _{SUD_PFU}	Clock to D input setup time	0.061	—	0.068	—	0.075	—	ns
t _{HD_PFU}	Clock to D input hold time	0.019	—	0.013	—	0.015	—	ns
t _{CK2Q_PFU}	Clock to Q delay, (D-type Register Configuration)	—	0.243	—	0.273	—	0.303	ns
PFU Dual Port Memory Mode Timing								
t _{CORAM_PFU}	Clock to Output (F Port)	—	0.710	—	0.803	—	0.897	ns
t _{SUDATA_PFU}	Data Setup Time	-0.137	—	-0.155	—	-0.174	—	ns
t _{HDATA_PFU}	Data Hold Time	0.188	—	0.217	—	0.246	—	ns
t _{SUADDR_PFU}	Address Setup Time	-0.227	—	-0.257	—	-0.286	—	ns
t _{HADDR_PFU}	Address Hold Time	0.240	—	0.275	—	0.310	—	ns
t _{SUWREN_PFU}	Write/Read Enable Setup Time	-0.055	—	-0.055	—	-0.063	—	ns
t _{HWREN_PFU}	Write/Read Enable Hold Time	0.059	—	0.059	—	0.071	—	ns
PIC Timing								
PIO Input/Output Buffer Timing								
t _{IN_PIO}	Input Buffer Delay (LVCMOS25)	—	0.423	—	0.466	—	0.508	ns
t _{OUT_PIO}	Output Buffer Delay (LVCMOS25)	—	1.241	—	1.301	—	1.361	ns
IOLOGIC Input/Output Timing								
t _{SUI_PIO}	Input Register Setup Time (Data Before Clock)	0.956	—	1.124	—	1.293	—	ns
t _{HI_PIO}	Input Register Hold Time (Data after Clock)	0.225	—	0.184	—	0.240	—	ns
t _{COO_PIO}	Output Register Clock to Output Delay ⁴	-	1.09	-	1.16	-	1.23	ns
t _{SUCE_PIO}	Input Register Clock Enable Setup Time	0.220	—	0.185	—	0.150	—	ns
t _{HCE_PIO}	Input Register Clock Enable Hold Time	-0.085	—	-0.072	—	-0.058	—	ns
t _{SULSR_PIO}	Set/Reset Setup Time	0.117	—	0.103	—	0.088	—	ns
t _{HLSR_PIO}	Set/Reset Hold Time	-0.107	—	-0.094	—	-0.081	—	ns
EBR Timing								
t _{CO_EBR}	Clock (Read) to output from Address or Data	—	2.78	—	2.89	—	2.99	ns
t _{COO_EBR}	Clock (Write) to output from EBR output Register	—	0.31	—	0.32	—	0.33	ns
t _{SUDATA_EBR}	Setup Data to EBR Memory	-0.218	—	-0.227	—	-0.237	—	ns
t _{HDATA_EBR}	Hold Data to EBR Memory	0.249	—	0.257	—	0.265	—	ns
t _{SUADDR_EBR}	Setup Address to EBR Memory	-0.071	—	-0.070	—	-0.068	—	ns
t _{HADDR_EBR}	Hold Address to EBR Memory	0.118	—	0.098	—	0.077	—	ns
t _{SUWREN_EBR}	Setup Write/Read Enable to EBR Memory	-0.107	—	-0.106	—	-0.106	—	ns

Figure 3-14. Jitter Transfer – 3.125 Gbps

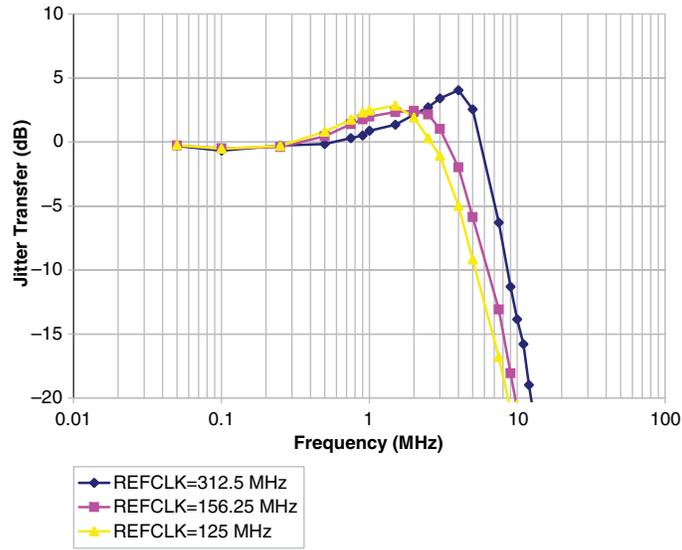
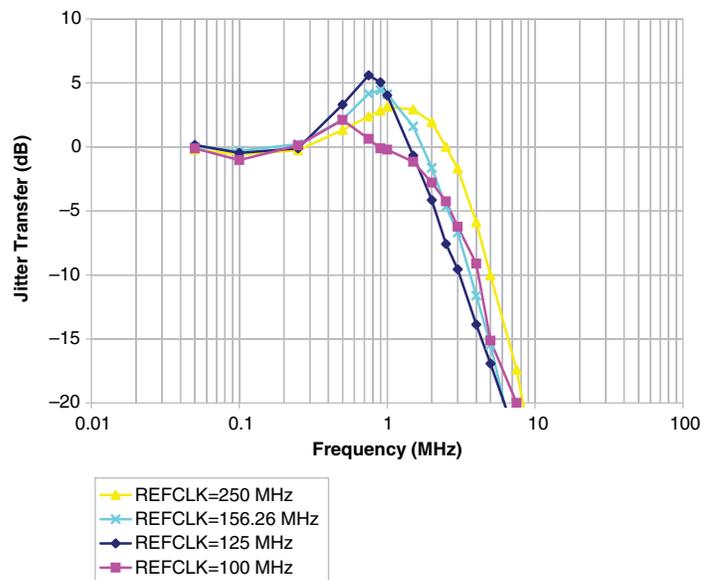


Figure 3-15. Jitter Transfer – 2.5 Gbps



XAUI/Serial Rapid I/O Type 3/CPRI LV E.30 Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-13. Transmit

Over Recommended Operating Conditions

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
T_{RF}	Differential rise/fall time	20%-80%	—	80	—	ps
$Z_{TX_DIFF_DC}$	Differential impedance		80	100	120	Ohms
$J_{TX_DDJ}^{2,3,4}$	Output data deterministic jitter		—	—	0.17	UI
$J_{TX_TJ}^{1,2,3,4}$	Total output data jitter		—	—	0.35	UI

1. Total jitter includes both deterministic jitter and random jitter.
2. Jitter values are measured with each CML output AC coupled into a 50-Ohm impedance (100-Ohm differential impedance).
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Values are measured at 2.5 Gbps.

Table 3-14. Receive and Jitter Tolerance

Over Recommended Operating Conditions

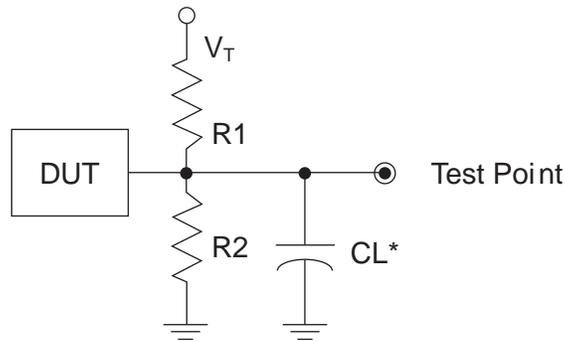
Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 3.125 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 3.125 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
$J_{RX_DJ}^{1,2,3}$	Deterministic jitter tolerance (peak-to-peak)		—	—	0.37	UI
$J_{RX_RJ}^{1,2,3}$	Random jitter tolerance (peak-to-peak)		—	—	0.18	UI
$J_{RX_SJ}^{1,2,3}$	Sinusoidal jitter tolerance (peak-to-peak)		—	—	0.10	UI
$J_{RX_TJ}^{1,2,3}$	Total jitter tolerance (peak-to-peak)		—	—	0.65	UI
T_{RX_EYE}	Receiver eye opening		0.35	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-18.
2. Jitter values are measured with each high-speed input AC coupled into a 50-Ohm impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance parameters are characterized when Full Rx Equalization is enabled.
5. Values are measured at 2.5 Gbps.

Switching Test Conditions

Figure 3-33 shows the output test load that is used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-23.

Figure 3-33. Output Test Load, LVTTTL and LVCMOS Standards



*CL Includes Test Fixture and Probe Capacitance

Table 3-23. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R ₁	R ₂	C _L	Timing Ref.	V _T
LVTTTL and other LVCMOS settings (L -> H, H -> L)	∞	∞	0 pF	LVCMOS 3.3 = 1.5V	—
				LVCMOS 2.5 = V _{CCIO} /2	—
				LVCMOS 1.8 = V _{CCIO} /2	—
				LVCMOS 1.5 = V _{CCIO} /2	—
				LVCMOS 1.2 = V _{CCIO} /2	—
LVCMOS 2.5 I/O (Z -> H)	∞	1MΩ	0 pF	V _{CCIO} /2	—
LVCMOS 2.5 I/O (Z -> L)	1 MΩ	∞	0 pF	V _{CCIO} /2	V _{CCIO}
LVCMOS 2.5 I/O (H -> Z)	∞	100	0 pF	V _{OH} - 0.10	—
LVCMOS 2.5 I/O (L -> Z)	100	∞	0 pF	V _{OL} + 0.10	V _{CCIO}

Note: Output test conditions for all other interfaces are determined by the respective standards.

Pin Information Summary

Pin Information Summary		ECP3-17EA			ECP3-35EA			ECP3-70EA		
Pin Type		256 ftBGA	328 csBGA	484 fpBGA	256 ftBGA	484 fpBGA	672 fpBGA	484 fpBGA	672 fpBGA	1156 fpBGA
General Purpose Inputs/Outputs per Bank	Bank 0	26	20	36	26	42	48	42	60	86
	Bank 1	14	10	24	14	36	36	36	48	78
	Bank 2	6	7	12	6	24	24	24	34	36
	Bank 3	18	12	44	16	54	59	54	59	86
	Bank 6	20	11	44	18	63	61	63	67	86
	Bank 7	19	26	32	19	36	42	36	48	54
	Bank 8	24	24	24	24	24	24	24	24	24
General Purpose Inputs per Bank	Bank 0	0	0	0	0	0	0	0	0	0
	Bank 1	0	0	0	0	0	0	0	0	0
	Bank 2	2	2	2	2	4	4	4	8	8
	Bank 3	0	0	0	2	4	4	4	12	12
	Bank 6	0	0	0	2	4	4	4	12	12
	Bank 7	4	4	4	4	4	4	4	8	8
	Bank 8	0	0	0	0	0	0	0	0	0
General Purpose Out- puts per Bank	Bank 0	0	0	0	0	0	0	0	0	0
	Bank 1	0	0	0	0	0	0	0	0	0
	Bank 2	0	0	0	0	0	0	0	0	0
	Bank 3	0	0	0	0	0	0	0	0	0
	Bank 6	0	0	0	0	0	0	0	0	0
	Bank 7	0	0	0	0	0	0	0	0	0
	Bank 8	0	0	0	0	0	0	0	0	0
Total Single-Ended User I/O		133	116	222	133	295	310	295	380	490
VCC		6	16	16	6	16	32	16	32	32
VCCAUX		4	5	8	4	8	12	8	12	16
VTT		4	7	4	4	4	4	4	4	8
VCCA		4	6	4	4	4	8	4	8	16
VCCPLL		2	2	4	2	4	4	4	4	4
VCCIO	Bank 0	2	3	2	2	2	4	2	4	4
	Bank 1	2	3	2	2	2	4	2	4	4
	Bank 2	2	2	2	2	2	4	2	4	4
	Bank 3	2	3	2	2	2	4	2	4	4
	Bank 6	2	3	2	2	2	4	2	4	4
	Bank 7	2	3	2	2	2	4	2	4	4
	Bank 8	1	2	2	1	2	2	2	2	2
VCCJ		1	1	1	1	1	1	1	1	1
TAP		4	4	4	4	4	4	4	4	4
GND, GNDIO		51	126	98	51	98	139	98	139	233
NC		0	0	73	0	0	96	0	0	238
Reserved ¹		0	0	2	0	2	2	2	2	2
SERDES		26	18	26	26	26	26	26	52	78
Miscellaneous Pins		8	8	8	8	8	8	8	8	8
Total Bonded Pins		256	328	484	256	484	672	484	672	1156

Part Number	Voltage	Grade ¹	Power	Package	Pins	Temp.	LUTs (K)
LFE3-70EA-6FN484C	1.2 V	-6	STD	Lead-Free fpBGA	484	COM	67
LFE3-70EA-7FN484C	1.2 V	-7	STD	Lead-Free fpBGA	484	COM	67
LFE3-70EA-8FN484C	1.2 V	-8	STD	Lead-Free fpBGA	484	COM	67
LFE3-70EA-6LFN484C	1.2 V	-6	LOW	Lead-Free fpBGA	484	COM	67
LFE3-70EA-7LFN484C	1.2 V	-7	LOW	Lead-Free fpBGA	484	COM	67
LFE3-70EA-8LFN484C	1.2 V	-8	LOW	Lead-Free fpBGA	484	COM	67
LFE3-70EA-6FN672C	1.2 V	-6	STD	Lead-Free fpBGA	672	COM	67
LFE3-70EA-7FN672C	1.2 V	-7	STD	Lead-Free fpBGA	672	COM	67
LFE3-70EA-8FN672C	1.2 V	-8	STD	Lead-Free fpBGA	672	COM	67
LFE3-70EA-6LFN672C	1.2 V	-6	LOW	Lead-Free fpBGA	672	COM	67
LFE3-70EA-7LFN672C	1.2 V	-7	LOW	Lead-Free fpBGA	672	COM	67
LFE3-70EA-8LFN672C	1.2 V	-8	LOW	Lead-Free fpBGA	672	COM	67
LFE3-70EA-6FN1156C	1.2 V	-6	STD	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-7FN1156C	1.2 V	-7	STD	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-8FN1156C	1.2 V	-8	STD	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-6LFN1156C	1.2 V	-6	LOW	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-7LFN1156C	1.2 V	-7	LOW	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-8LFN1156C	1.2 V	-8	LOW	Lead-Free fpBGA	1156	COM	67

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade ¹	Power	Package	Pins	Temp.	LUTs (K)
LFE3-95EA-6FN484C	1.2 V	-6	STD	Lead-Free fpBGA	484	COM	92
LFE3-95EA-7FN484C	1.2 V	-7	STD	Lead-Free fpBGA	484	COM	92
LFE3-95EA-8FN484C	1.2 V	-8	STD	Lead-Free fpBGA	484	COM	92
LFE3-95EA-6LFN484C	1.2 V	-6	LOW	Lead-Free fpBGA	484	COM	92
LFE3-95EA-7LFN484C	1.2 V	-7	LOW	Lead-Free fpBGA	484	COM	92
LFE3-95EA-8LFN484C	1.2 V	-8	LOW	Lead-Free fpBGA	484	COM	92
LFE3-95EA-6FN672C	1.2 V	-6	STD	Lead-Free fpBGA	672	COM	92
LFE3-95EA-7FN672C	1.2 V	-7	STD	Lead-Free fpBGA	672	COM	92
LFE3-95EA-8FN672C	1.2 V	-8	STD	Lead-Free fpBGA	672	COM	92
LFE3-95EA-6LFN672C	1.2 V	-6	LOW	Lead-Free fpBGA	672	COM	92
LFE3-95EA-7LFN672C	1.2 V	-7	LOW	Lead-Free fpBGA	672	COM	92
LFE3-95EA-8LFN672C	1.2 V	-8	LOW	Lead-Free fpBGA	672	COM	92
LFE3-95EA-6FN1156C	1.2 V	-6	STD	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-7FN1156C	1.2 V	-7	STD	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-8FN1156C	1.2 V	-8	STD	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-6LFN1156C	1.2 V	-6	LOW	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-7LFN1156C	1.2 V	-7	LOW	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-8LFN1156C	1.2 V	-8	LOW	Lead-Free fpBGA	1156	COM	92

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.